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(54) Title: LIGHT EMITTING DEVICE ARRAY

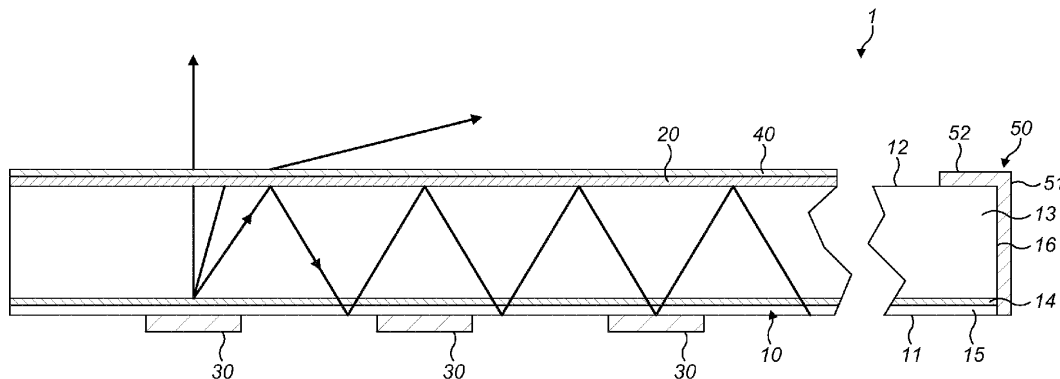


FIG. 1

(57) **Abstract:** A light emitting device array is provided. The light emitting device array comprises a light emitting stack, a first electrical contact layer, an array of second electrical contacts, and an anti-reflection layer. The light emitting stack has a light emitting surface and a contact surface. The light emitting surface and the contact surface define opposing sides of the light emitting stack. The light emitting stack comprises a plurality of Group III-nitride layers including a first semiconducting layer provided towards the light emitting surface of the light emitting stack, a second semiconducting layer provided towards the contact surface, and an active layer arranged between the first semiconducting layer and the second semiconducting layer, the active layer configured to generate light having a first wavelength. The light emitting surface and the contact surface are parallel to each other and aligned with the plurality of Group III-nitride layers. The first electrical contact layer is provided on the light emitting stack and is configured to be in electrical contact with the first semiconducting layer. The array of second electrical contacts is provided on the contact surface of the light emitting stack. Each second electrical contact defines a light emitting device between the first semiconducting layer and the second electrical contact. Each of the second electrical contacts is spaced apart from the other second electrical contacts to form a two-dimensional array of light emitting devices. The anti-reflection layer is provided on the light emitting surface. The anti-reflection layer is configured to increase a light extraction efficiency of the light generated by the light emitting stack.

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